



N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
30V	20A	28 @ V _{GS} =10V
		38 @ V _{GS} =4.5V

FEATURES

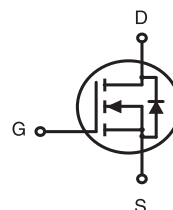
- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	20
		T _C =70°C	16.3
I _{DM}	-Pulsed ^b	80	A
E _{AS}	Single Pulse Avalanche Energy ^d	8.8	mJ
P _D	Maximum Power Dissipation ^a	T _C =25°C	21
		T _C =70°C	13.3
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case ^a	6	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

STU/D330S

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.9	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =20A		22	28	m ohm
		V _{GS} =4.5V , I _D =17.5A		28	38	m ohm
g _{FS}	Forward Transconductance	V _{DS} =15V , I _D =20A		15		S
DYNAMIC CHARACTERISTICS [°]						
C _{ISS}	Input Capacitance	V _{DS} =15V,V _{GS} =0V f=1.0MHz		478		pF
C _{OSS}	Output Capacitance			100		pF
C _{RSS}	Reverse Transfer Capacitance			65		pF
SWITCHING CHARACTERISTICS [°]						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =15V I _D =1A V _{GS} =10V R _{GEN} =6 ohm		10.5		ns
t _r	Rise Time			10		ns
t _{D(OFF)}	Turn-Off Delay Time			17		ns
t _f	Fall Time			20		ns
Q _g	Total Gate Charge	V _{DS} =15V,I _D =20A,V _{GS} =10V		8.1		nC
		V _{DS} =15V,I _D =20A,V _{GS} =4.5V		4		nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V,I _D =20A,		1.3		nC
Q _{gd}	Gate-Drain Charge	V _{GS} =10V		2.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				1.7	A
V _{SD}	Diode Forward Voltage [°]	V _{GS} =0V,I _S =1.7A		0.79	1.2	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 20V. (See Figure13)

Sep,03,2008

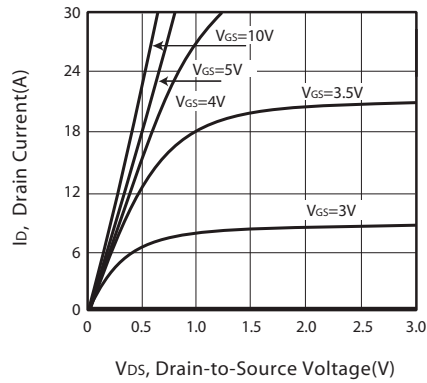


Figure 1. Output Characteristics

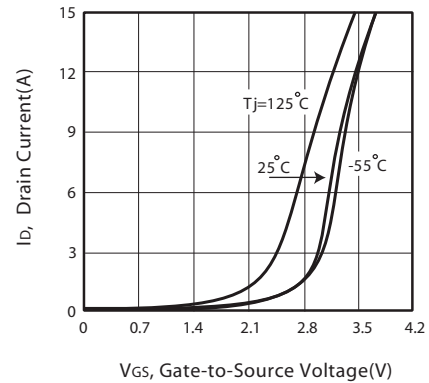


Figure 2. Transfer Characteristics

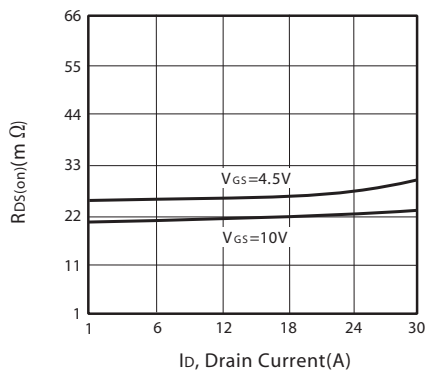


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

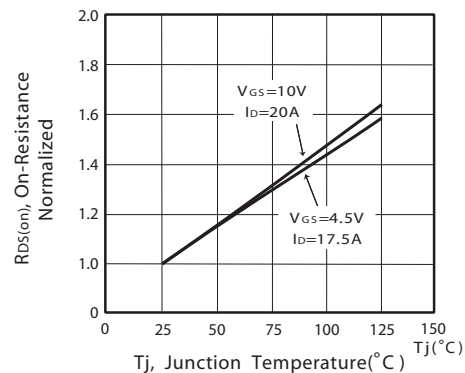


Figure 4. On-Resistance Variation with Drain Current and Temperature

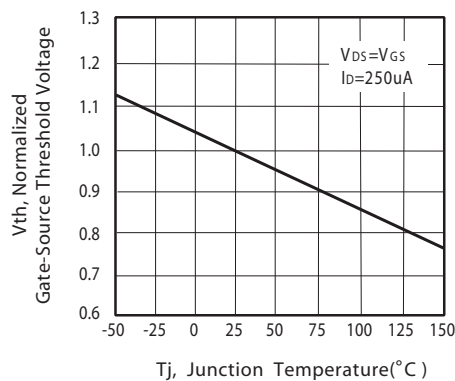


Figure 5. Gate Threshold Variation with Temperature

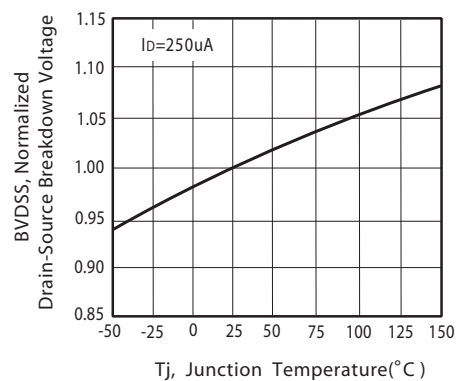


Figure 6. Breakdown Voltage Variation with Temperature

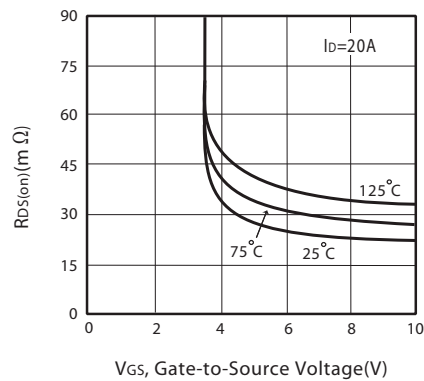


Figure 7. On-Resistance vs. Gate-Source Voltage

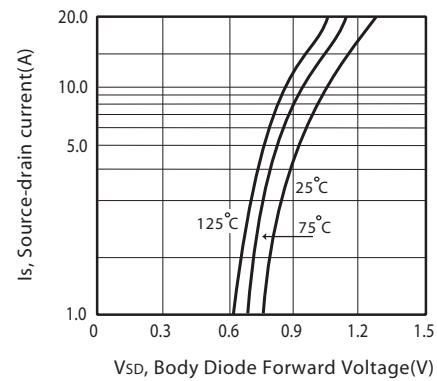


Figure 8. Body Diode Forward Voltage Variation with Source Current

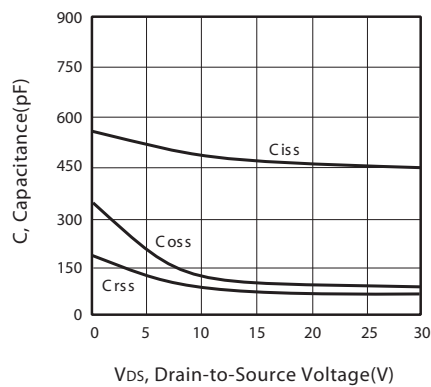


Figure 9. Capacitance

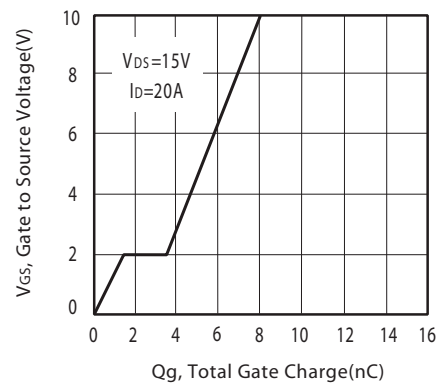


Figure 10. Gate Charge

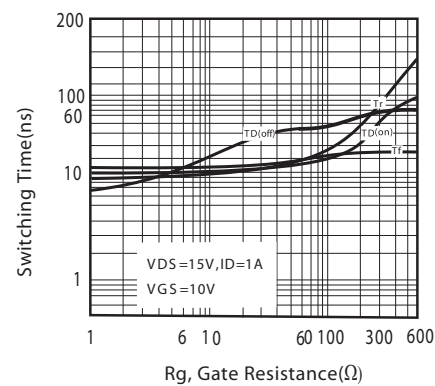


Figure 11. switching characteristics

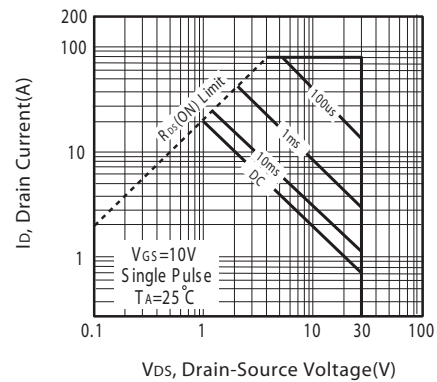
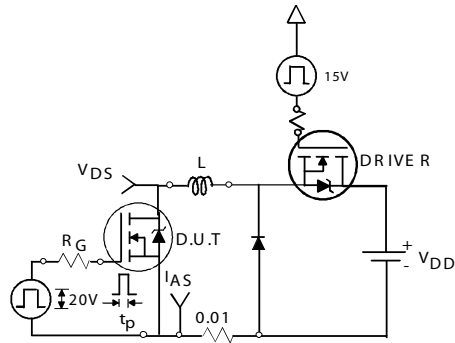
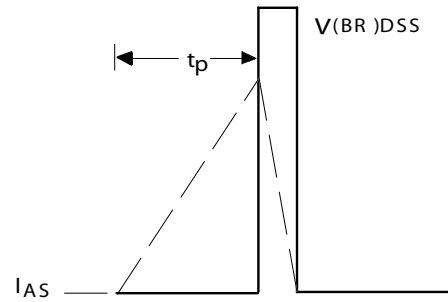


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

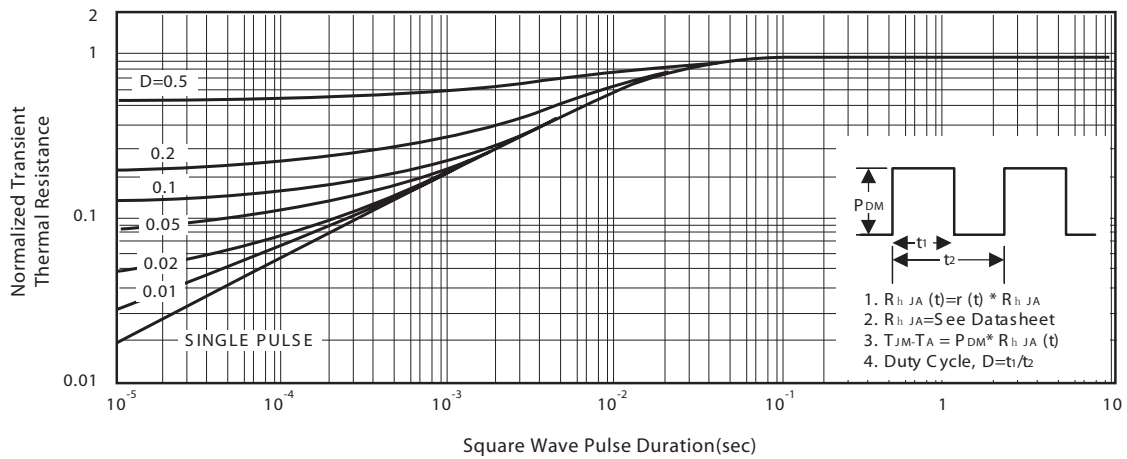
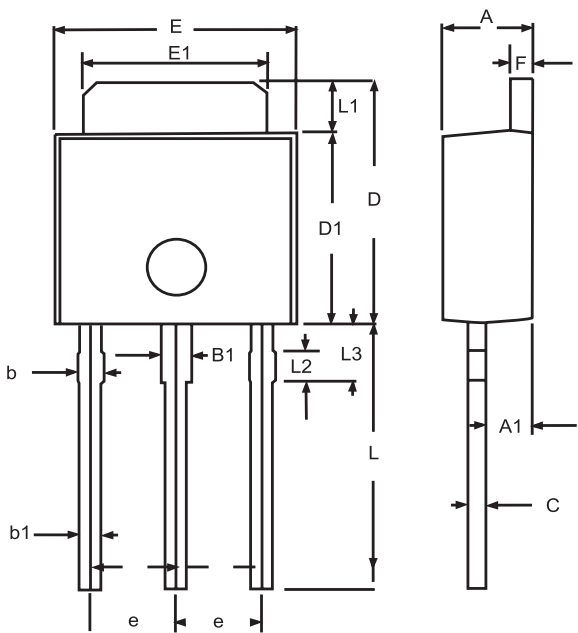


Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0.32
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

